

PLEASE AMEND THE CLAIMS AS FOLLOWS:

19. (TWICE AMENDED) A cylindrical shaped, capacitor structure,
featuring a cylindrical storage node structure comprised
of an underlying, uniformly doped, cylindrical
polysilicon shape and an overlying agglomerated metal
silicide layer, comprising:

10 said cylindrical polysilicon shape comprised of a bottom polysilicon shape located on a first section of a top surface of an underlying planar, insulator layer, with said bottom polysilicon shape overlying and contacting a top surface of a plug structure which in turn is located in an opening in said insulator layer, and with said cylindrical polysilicon shape comprised of uniformly doped, vertical polysilicon shapes, located overlying second sections of said planar, insulator layer, with bottom portions of said vertical polysilicon shapes butting edges of said bottom polysilicon shape;

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5 said agglomerated metal silicide layer, with a
 roughened top surface, located on exposed portions of said
 cylindrical polysilicon shape, featuring agglomerated
 metal silicide on top surface of said bottom polysilicon
 shape, and on all surfaces of uniformly doped, said
 vertical polysilicon shapes, resulting in said
 cylindrical shape storage node structure comprised of
 said agglomerated metal silicide layer on said
 cylindrical polysilicon shape;

10 a capacitor dielectric layer located on the
 exposed surfaces of said cylindrical shape storage node
 structure; and

 an upper electrode, covering said capacitor
 dielectric layer.
